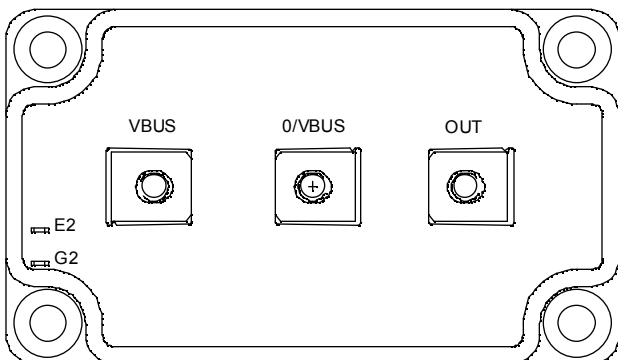
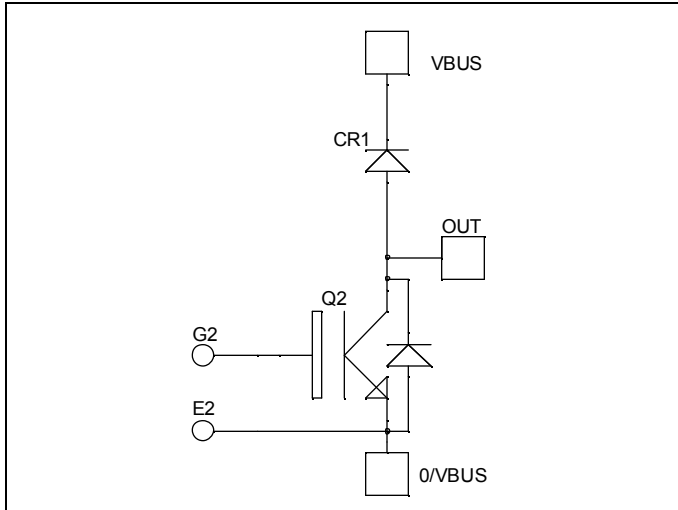


**Boost chopper
Fast Trench + Field Stop IGBT®
Power Module**

www.datasheet4u.com

**$V_{CES} = 1200V$
 $I_C = 300A @ T_c = 80^\circ C$**



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Fast Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	420
		$T_C = 80^\circ C$	300
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	600
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	1380
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	600A @ 1100V



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 1200\text{V}$			500	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 300\text{A}$	$T_j = 25^\circ\text{C}$ 1.4	$T_j = 25^\circ\text{C}$ 1.7	$T_j = 25^\circ\text{C}$ 2.1	V
			$T_j = 125^\circ\text{C}$	2.0		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		21		nF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		1.2		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.9		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 300\text{A}$ $R_G = 1.8\Omega$		260		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			420		
T_f	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 300\text{A}$ $R_G = 1.8\Omega$		290		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			520		
T_f	Fall Time			90		
E_{on}	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 600\text{V}$	$T_j = 125^\circ\text{C}$	30		mJ
E_{off}	Turn off Energy	$I_C = 300\text{A}$ $R_G = 1.8\Omega$	$T_j = 125^\circ\text{C}$	30		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$			$T_j = 25^\circ\text{C}$ 500 $T_j = 125^\circ\text{C}$ 700	μA
I_F	DC Forward Current			300		A
V_F	Diode Forward Voltage	$I_F = 300\text{A}$ $V_{GE} = 0\text{V}$		$T_j = 25^\circ\text{C}$ 1.6 $T_j = 125^\circ\text{C}$ 1.6	2.1	V
t_{rr}	Reverse Recovery Time	$I_F = 300\text{A}$ $V_R = 600\text{V}$ $di/dt = 3000\text{A}/\mu\text{s}$		$T_j = 25^\circ\text{C}$ 170 $T_j = 125^\circ\text{C}$ 280		ns
Q_{rr}	Reverse Recovery Charge			$T_j = 25^\circ\text{C}$ 27 $T_j = 125^\circ\text{C}$ 54		μC
E_r	Reverse Recovery Energy			$T_j = 25^\circ\text{C}$ 15 $T_j = 125^\circ\text{C}$ 27		mJ

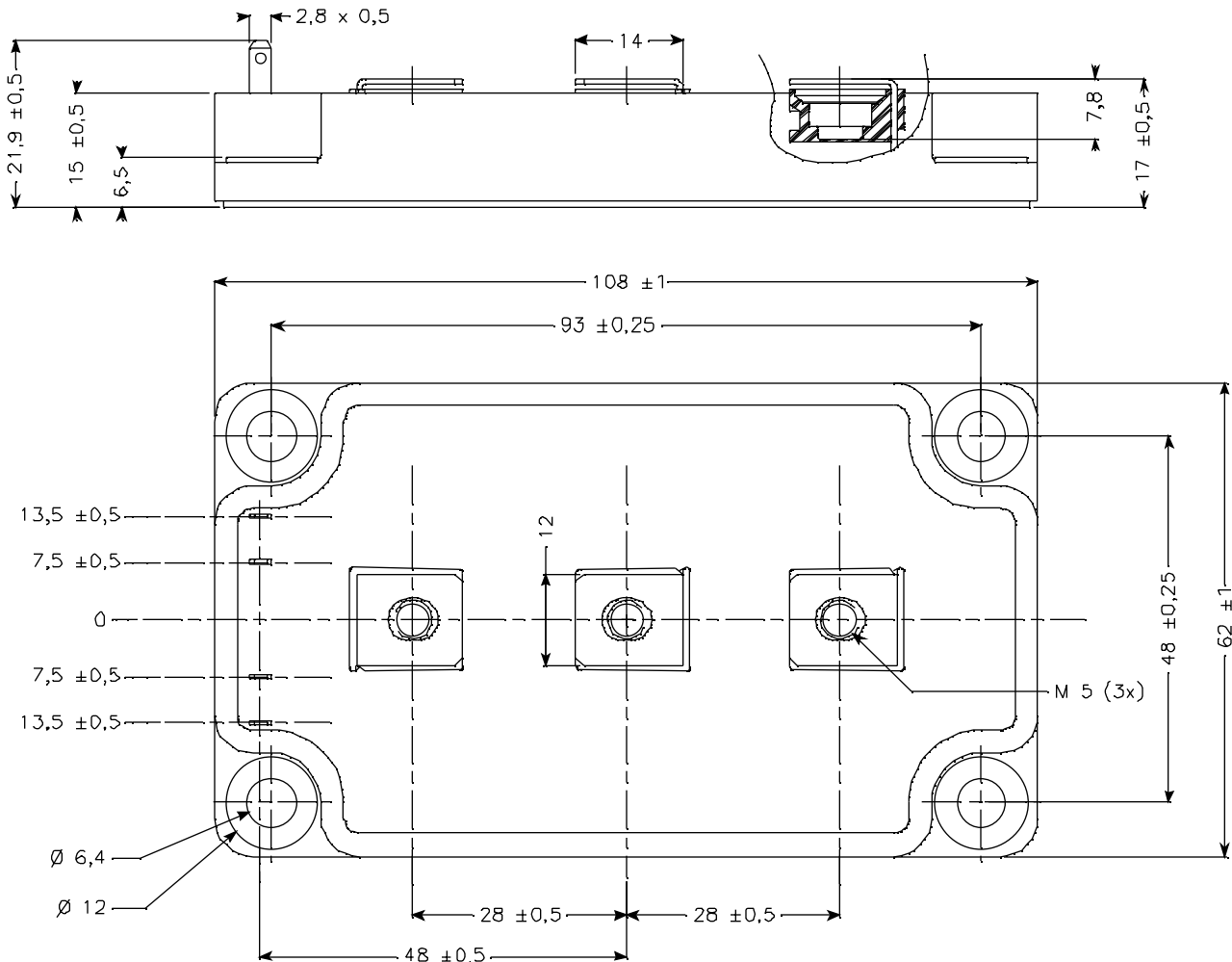
Thermal and package characteristics

Symbol Characteristic

Min Typ Max Unit

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.09	°C/W	
		Diode		0.17		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight			280	g	

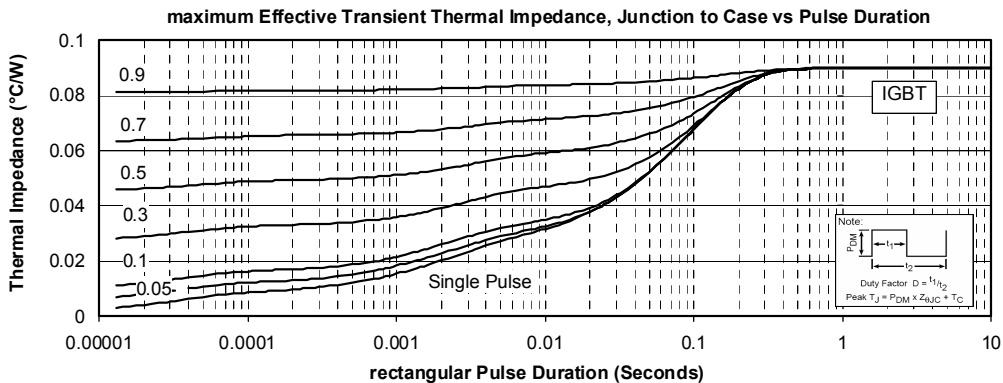
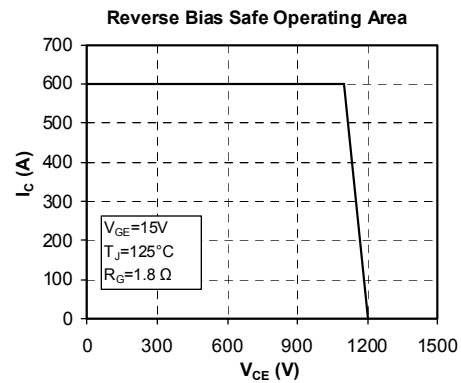
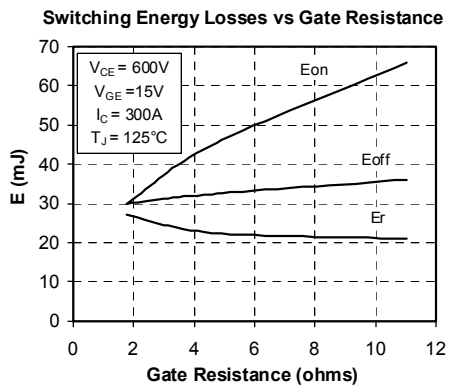
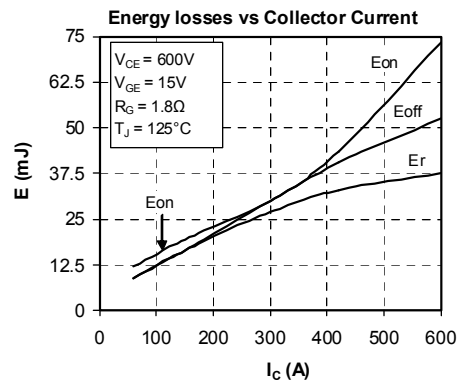
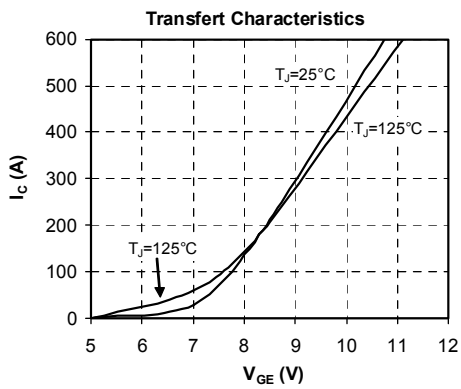
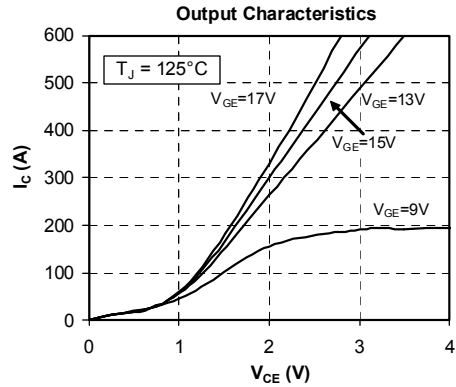
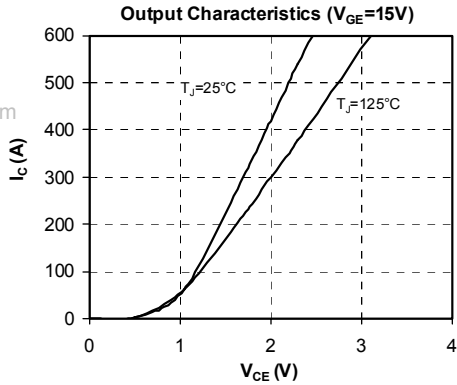
SP6 Package outline (dimensions in mm)



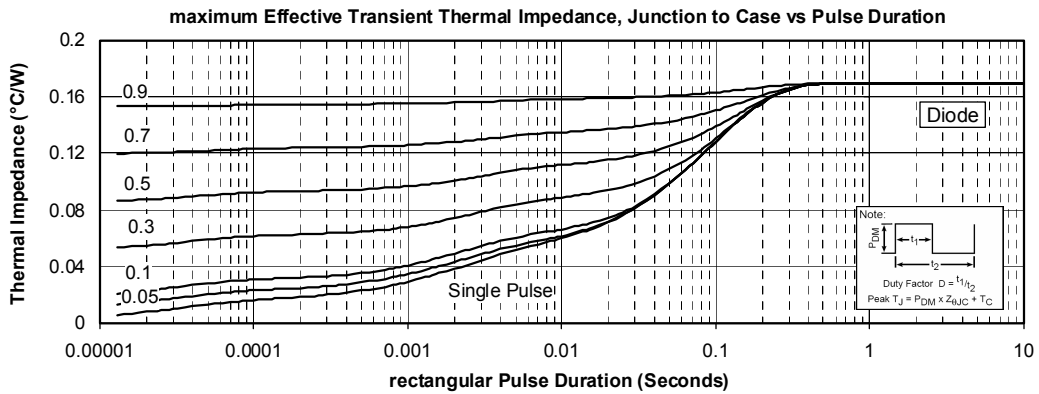
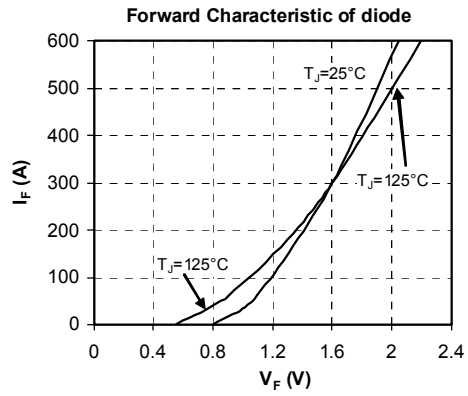
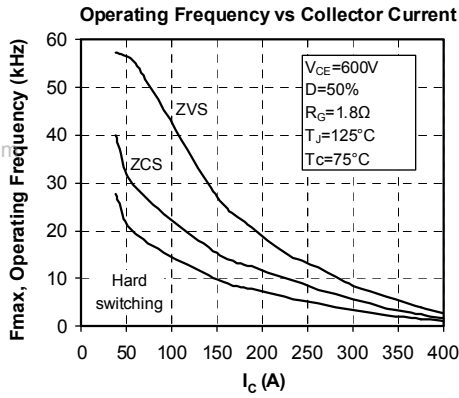
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve

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